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Inclosure Material:
Metal
Overall Length:
0.422 inches
Mounting Facility Quantity:
1
Internal Configuration:
Junction contact
Electrode Internally-electrically Connected To Case:
Anode
Mounting Method:
Threaded stud
Features Provided:
Hermetically sealed case
Overall Width Across Flats:
0.547 inches
Thread Size:
0.250 inches
Semiconductor Material:
Silicon
Voltage Rating In Volts Per Characteristic:
100.0 breakover voltage, dc
Current Rating Per Characteristic:
13.00 amperes source cutoff current
Power Rating Per Characteristic:
500.0 milliwatts small-signal input power, common-collector blank
Maximum Operating Tempurature Per Measurement Point:
125.0 degrees celsius case
Special Features:
Junction pattern arrangement: pnpn
Thread Series Designator:
Unf
Terminal Type And Quantity:
1 threaded stud and 2 tab, solder lug
Specification Data:
80131-release3705 professional/industrial association specification
Shelf Life:
N/a
Unit Of Measure:
Demilitarization:
No

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